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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104faafp-x0

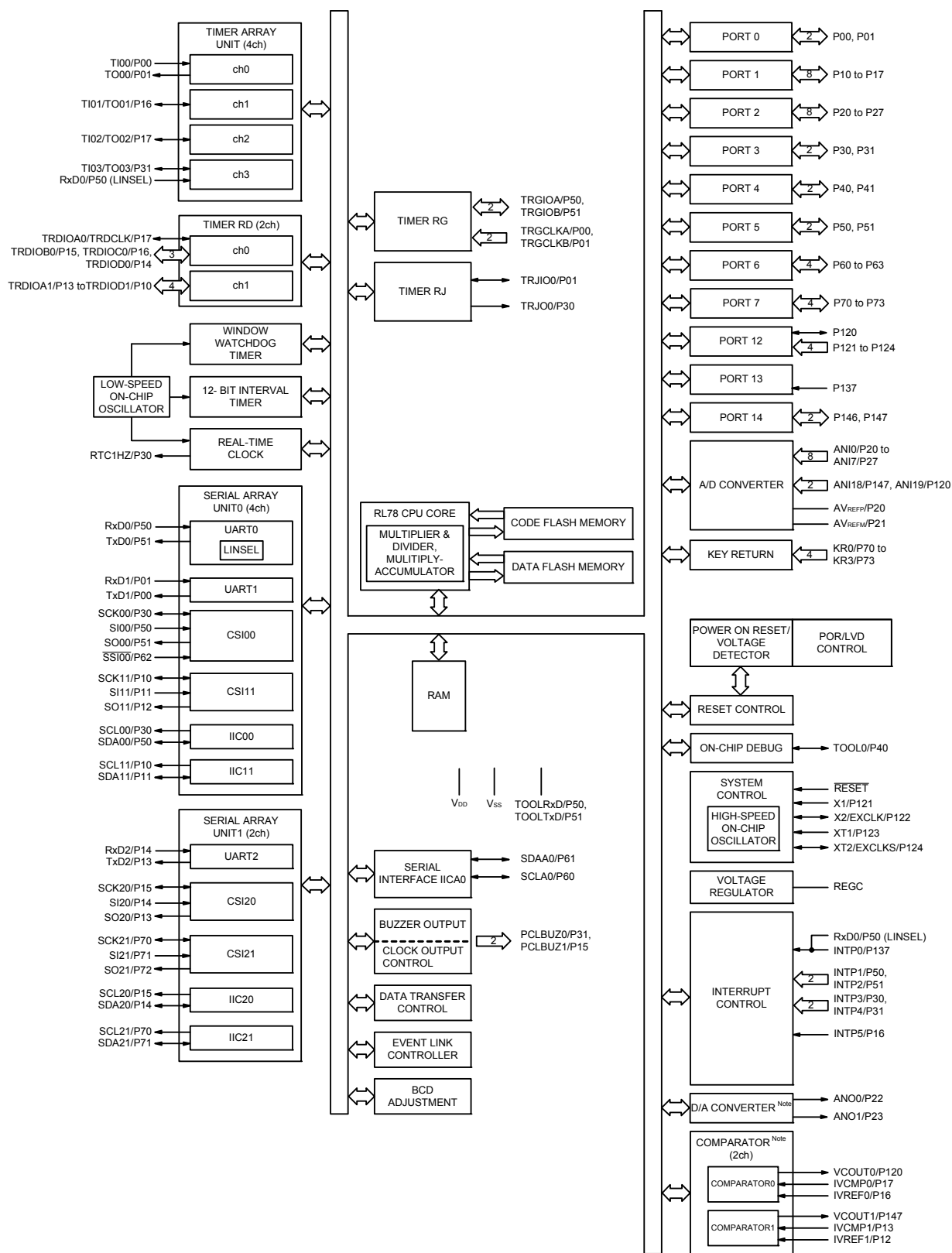
(5/5)

Pin count	Package	Fields of Application Note	Ordering Part Number
80 pins	80-pin plastic LQFP (12 × 12 mm, 0.5 mm pitch)	A	R5F104MFAFB#V0, R5F104MGAFB#V0, R5F104MHAFA#V0, R5F104MJAFB#V0 R5F104MFAFB#X0, R5F104MGAFB#X0, R5F104MHAFA#X0, R5F104MJAFB#X0 R5F104MKAFB#30, R5F104MLAFB#30 R5F104MKAFB#50, R5F104MLAFB#50
		D	R5F104MFDFA#V0, R5F104MGDFA#V0, R5F104MHDFA#V0, R5F104MJDFB#V0 R5F104MFDFA#X0, R5F104MGDFA#X0, R5F104MHDFA#X0, R5F104MJDFB#X0
		G	R5F104MFGFB#V0, R5F104MGGFB#V0, R5F104MHGFB#V0, R5F104MJGFB#V0 R5F104MFGFB#X0, R5F104MGGFB#X0, R5F104MHGFB#X0, R5F104MJGFB#X0 R5F104MKGFB#30, R5F104MLGFB#30 R5F104MKGFB#50, R5F104MLGFB#50
	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	A	R5F104MFAFA#V0, R5F104MGFAFA#V0, R5F104MHAFA#V0, R5F104MJFAFA#V0 R5F104MFAFA#X0, R5F104MGFAFA#X0, R5F104MHAFA#X0, R5F104MJFAFA#X0 R5F104MKFAFA#30, R5F104MLFAFA#30 R5F104MKFAFA#50, R5F104MLFAFA#50
		D	R5F104MFDFA#V0, R5F104MGDFA#V0, R5F104MHDFA#V0, R5F104MJDFB#V0 R5F104MFDFA#X0, R5F104MGDFA#X0, R5F104MHDFA#X0, R5F104MJDFB#X0
		G	R5F104MFGFA#V0, R5F104MGGFA#V0, R5F104MHGFA#V0, R5F104MJGFA#V0 R5F104MFGFA#X0, R5F104MGGFA#X0, R5F104MHGFA#X0, R5F104MJGFA#X0 R5F104MKGFA#30, R5F104MLGFA#30 R5F104MKGFA#50, R5F104MLGFA#50
100 pins	100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)	A	R5F104PFAFB#V0, R5F104PGAFA#V0, R5F104PHAFA#V0, R5F104PJAFB#V0 R5F104PFAFB#X0, R5F104PGAFA#X0, R5F104PHAFA#X0, R5F104PJAFB#X0 R5F104PKAFB#30, R5F104PLAFB#30 R5F104PKAFB#50, R5F104PLAFB#50
		D	R5F104PFDFA#V0, R5F104PGDFA#V0, R5F104PHDFA#V0, R5F104PJDFB#V0 R5F104PFDFA#X0, R5F104PGDFA#X0, R5F104PHDFA#X0, R5F104PJDFB#X0
		G	R5F104PFGFB#V0, R5F104PGGFB#V0, R5F104PHGFB#V0, R5F104PJGFB#V0 R5F104PFGFB#X0, R5F104PGGFB#X0, R5F104PHGFB#X0, R5F104PJGFB#X0 R5F104PKGFB#30, R5F104PLGFB#30 R5F104PKGFB#50, R5F104PLGFB#50
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	A	R5F104PFAFA#V0, R5F104PGAFA#V0, R5F104PHAFA#V0, R5F104PJFAFA#V0 R5F104PFAFA#X0, R5F104PGAFA#X0, R5F104PHAFA#X0, R5F104PJFAFA#X0 R5F104PKFAFA#30, R5F104PLFAFA#30 R5F104PKFAFA#50, R5F104PLFAFA#50
		D	R5F104PFDFA#V0, R5F104PGDFA#V0, R5F104PHDFA#V0, R5F104PJDFB#V0 R5F104PFDFA#X0, R5F104PGDFA#X0, R5F104PHDFA#X0, R5F104PJDFB#X0
		G	R5F104PFGFA#V0, R5F104PGGFA#V0, R5F104PHGFA#V0, R5F104PJGFA#V0 R5F104PFGFA#X0, R5F104PGGFA#X0, R5F104PHGFA#X0, R5F104PJGFA#X0 R5F104PKGFA#30, R5F104PLGFA#30 R5F104PKGFA#50, R5F104PLGFA#50

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

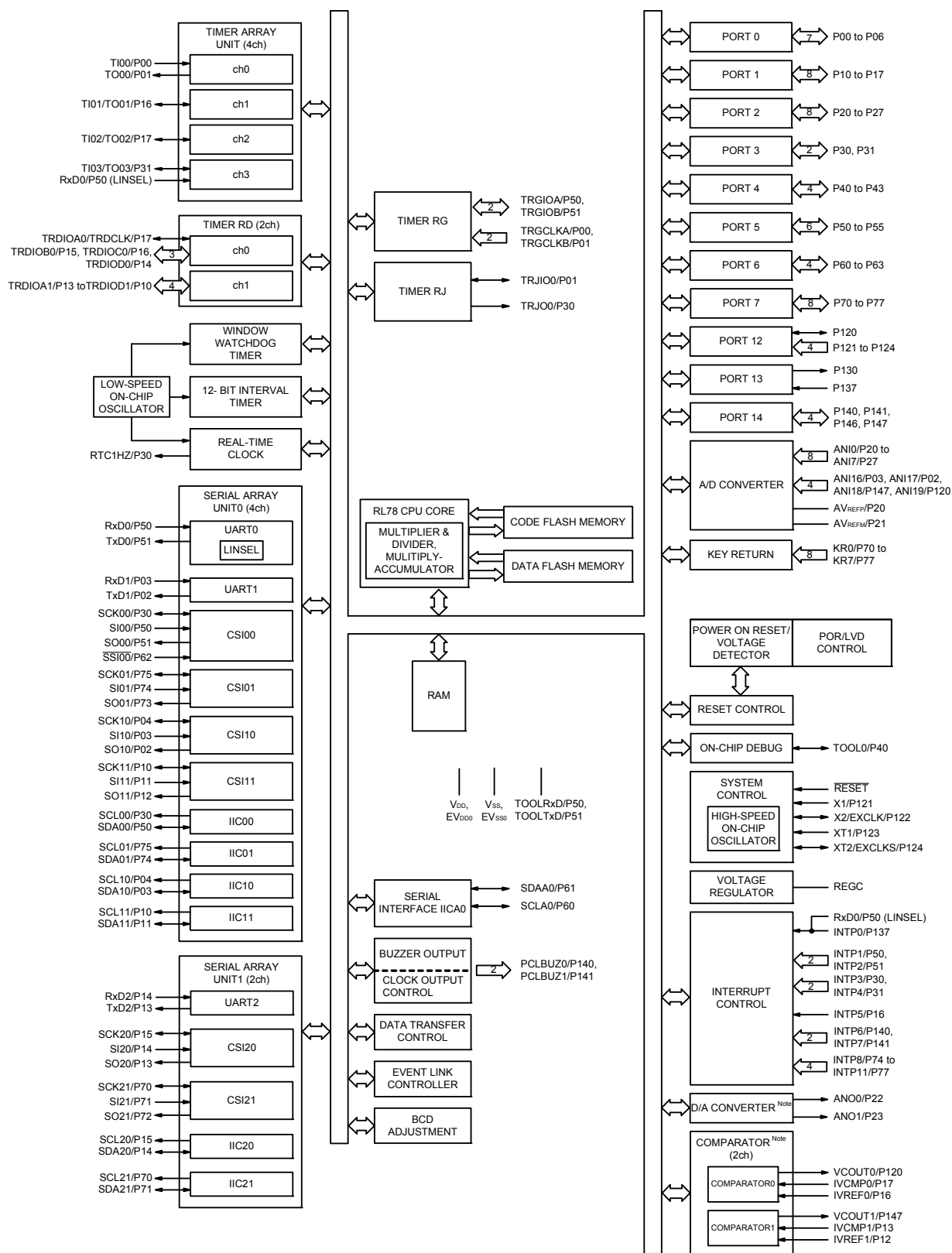
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.5.5 44-pin products



Note Mounted on the 96 KB or more code flash memory products.

1.5.8 64-pin products



Note Mounted on the 96 KB or more code flash memory products.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xD (x = A to C, E to G, J, L): Start address FE900H
R5F104xE (x = A to C, E to G, J, L): Start address FE900H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

[80-pin, 100-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		80-pin	100-pin
		R5F104Mx (x = K, L)	R5F104Px (x = K, L)
Code flash memory (KB)		384 to 512	384 to 512
Data flash memory (KB)		8	8
RAM (KB)		32 to 48 Note	32 to 48 Note
Address space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)	
	High-speed on-chip oscillator clock (f _{IH})	HS (high-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V _{DD} = 1.6 to 5.5 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f _{IH} = 32 MHz operation)	
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)	
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)	
Instruction set		<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 	
I/O port	Total	74	92
	CMOS I/O	64	82
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)	
	Watchdog timer	1 channel	
	Real-time clock (RTC)	1 channel	
	12-bit interval timer	1 channel	
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels	
	RTC output	1 • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)	

Note In the case of the 48 KB, this is about 47 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

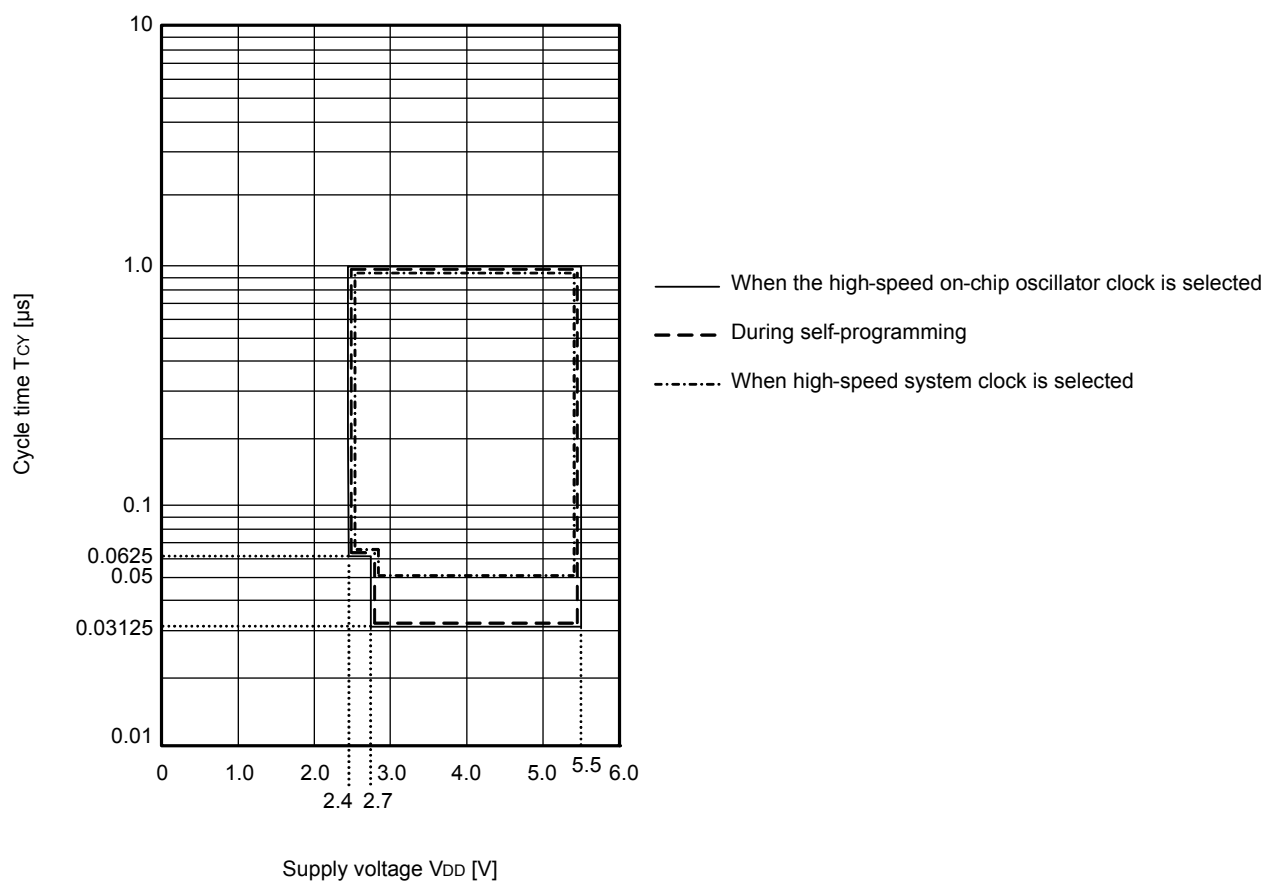
(TA = -40 to +85°C, 1.6 V ≤ EVDD0 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = 0 V)

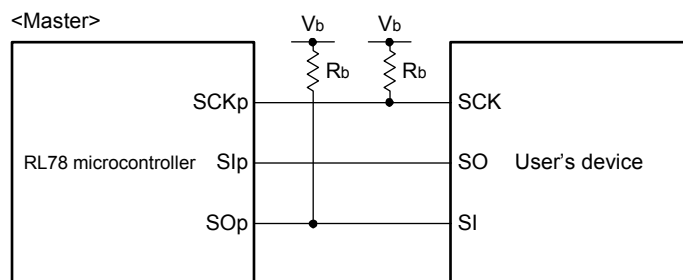
Parameter	Symbol	Conditions						MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD1	Operating mode	HS (high-speed main) mode Note 5	fHOCO = 64 MHz, fIH = 32 MHz Note 3	Basic operation	VDD = 5.0 V		2.4			mA
						VDD = 3.0 V		2.4			
				fHOCO = 32 MHz, fIH = 32 MHz Note 3	Basic operation	VDD = 5.0 V		2.1			
						VDD = 3.0 V		2.1			
			HS (high-speed main) mode Note 5	fHOCO = 64 MHz, fIH = 32 MHz Note 3	Normal operation	VDD = 5.0 V		5.1	8.7		mA
						VDD = 3.0 V		5.1	8.7		
				fHOCO = 32 MHz, fIH = 32 MHz Note 3	Normal operation	VDD = 5.0 V		4.8	8.1		
						VDD = 3.0 V		4.8	8.1		
				fHOCO = 48 MHz, fIH = 24 MHz Note 3	Normal operation	VDD = 5.0 V		4.0	6.9		
						VDD = 3.0 V		4.0	6.9		
				fHOCO = 24 MHz, fIH = 24 MHz Note 3	Normal operation	VDD = 5.0 V		3.8	6.3		
						VDD = 3.0 V		3.8	6.3		
				fHOCO = 16 MHz, fIH = 16 MHz Note 3	Normal operation	VDD = 5.0 V		2.8	4.6		
						VDD = 3.0 V		2.8	4.6		
			LS (low-speed main) mode Note 5	fHOCO = 8 MHz, fIH = 8 MHz Note 3	Normal operation	VDD = 3.0 V		1.3	2.0		mA
						VDD = 2.0 V		1.3	2.0		
			LV (low-voltage main) mode Note 5	fHOCO = 4 MHz, fIH = 4 MHz Note 3	Normal operation	VDD = 3.0 V		1.3	1.8		mA
						VDD = 2.0 V		1.3	1.8		
			HS (high-speed main) mode Note 5	fMX = 20 MHz Note 2, VDD = 5.0 V	Normal operation	Square wave input		3.3	5.3		mA
						Resonator connection		3.4	5.5		
				fMX = 20 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		3.3	5.3		
						Resonator connection		3.4	5.5		
				fMX = 10 MHz Note 2, VDD = 5.0 V	Normal operation	Square wave input		2.0	3.1		
						Resonator connection		2.1	3.2		
				fMX = 10 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		2.0	3.1		
						Resonator connection		2.1	3.2		
			LS (low-speed main) mode Note 5	fMX = 8 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		1.2	1.9		mA
						Resonator connection		1.2	2.0		
				fMX = 8 MHz Note 2, VDD = 2.0 V	Normal operation	Square wave input		1.2	1.9		
						Resonator connection		1.2	2.0		
			Subsystem clock operation	fSUB = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		4.7	6.1		μA
						Resonator connection		4.7	6.1		
				fSUB = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		4.7	6.1		
						Resonator connection		4.7	6.1		
				fSUB = 32.768 kHz Note 4 TA = +50°C	Normal operation	Square wave input		4.8	6.7		
						Resonator connection		4.8	6.7		
				fSUB = 32.768 kHz Note 4 TA = +70°C	Normal operation	Square wave input		4.8	7.5		
						Resonator connection		4.8	7.5		
				fSUB = 32.768 kHz Note 4 TA = +85°C	Normal operation	Square wave input		5.4	8.9		
						Resonator connection		5.4	8.9		

(Notes and Remarks are listed on the next page.)

- Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or VSS, EVSS0, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3.** When high-speed system clock and subsystem clock are stopped.
- Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
- | | |
|-----------------------------|-------------------------------------|
| HS (high-speed main) mode: | 2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz |
| | 2.4 V ≤ VDD ≤ 5.5 V@1 MHz to 16 MHz |
| LS (low-speed main) mode: | 1.8 V ≤ VDD ≤ 5.5 V@1 MHz to 8 MHz |
| LV (low-voltage main) mode: | 1.6 V ≤ VDD ≤ 5.5 V@1 MHz to 4 MHz |
- Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

Minimum Instruction Execution Time during Main System Clock Operation

T_{CY} vs V_{DD} (HS (high-speed main) mode)

CSI mode connection diagram (during communication at different potential)

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Standard mode: f _{CLK} ≥ 1 MHz	2.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.8 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		0	100	0	100	kHz
Setup time of restart condition	t _{SU: STA}	2.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.7		4.7		μs
Hold time ^{Note 1}	t _{HD: STA}	2.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.0		4.0		μs
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.7		4.7		μs
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		4.0		4.0		μs

(Notes, Caution, and Remark are listed on the next page.)

- (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +85°C, 2.4 V ≤ VDD ≤ 5.5 V, 1.6 V ≤ EVDD = EVDD1 ≤ VDD, VSS = EVSS0 = EVSS1 = 0 V, Reference voltage (+) = VBGR ^{Note 3}, Reference voltage (-) = AVREFM = 0 V ^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	tCONV	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±0.60	% FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±1.0	LSB
Analog input voltage	VAIN			0		VBGR ^{Note 3}	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = VSS, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(4/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA		EVDD0 - 0.7	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -2.0 mA		EVDD0 - 0.6	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -1.5 mA		EVDD0 - 0.5	V
	VOH2	P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA		VDD - 0.5	V
Output voltage, low	VOL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 8.5 mA		0.7	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 3.0 mA		0.6	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 1.5 mA		0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 0.6 mA		0.4	V
	VOL2	P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V, IOL2 = 400 μA		0.4	V
	VOL3	P60 to P63	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 15.0 mA		2.0	V
			4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 5.0 mA		0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 3.0 mA		0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 2.0 mA		0.4	V

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or VSS, EVSS0, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3.** When high-speed system clock and subsystem clock are stopped.
- Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
- HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$

Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD2 Note 2	HALT mode Note 7	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.79	4.86	mA
					VDD = 3.0 V		0.79	4.86	
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.49	4.17	
					VDD = 3.0 V		0.49	4.17	
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.62	3.82	
					VDD = 3.0 V		0.62	3.82	
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.4	3.25	
					VDD = 3.0 V		0.4	3.25	
				fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.38	2.28	
					VDD = 3.0 V		0.38	2.28	
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.30	2.65	mA
					Resonator connection		0.40	2.77	
				fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.30	2.65	
					Resonator connection		0.40	2.77	
				fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.20	1.36	
					Resonator connection		0.25	1.46	
				fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.20	1.36	
					Resonator connection		0.25	1.46	
	IDD3 Note 6	STOP mode Note 8	Subsystem clock operation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.28	0.66	μA
					Resonator connection		0.47	0.85	
				fSUB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.34	0.66	
					Resonator connection		0.53	0.85	
				fSUB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.37	2.35	
					Resonator connection		0.56	2.54	
				fSUB = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.61	4.08	
					Resonator connection		0.80	4.27	
				fSUB = 32.768 kHz Note 5, TA = +85°C	Square wave input		1.55	8.09	
					Resonator connection		1.74	8.28	
				fSUB = 32.768 kHz Note 5, TA = +105°C	Square wave input		6.00	51.00	
					Resonator connection		6.00	51.00	
				TA = -40°C			0.19	0.57	μA
				TA = +25°C			0.25	0.57	
				TA = +50°C			0.33	2.26	
				TA = +70°C			0.52	3.99	
				TA = +85°C			1.46	8.00	
				TA = +105°C			5.50	50.00	

(Notes and Remarks are listed on the next page.)

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)**(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tkCY2	4.0 V ≤ EVDD0 ≤ 5.5 V	20 MHz < fMCK	16/fMCK		ns
			fMCK ≤ 20 MHz	12/fMCK		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	16 MHz < fMCK	16/fMCK		ns
			fMCK ≤ 16 MHz	12/fMCK		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		12/fMCK and 1000		ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 14		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 16		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 36		ns
Slp setup time (to SCKp↑) Note 1	tSIK2	2.7 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 40		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 60		ns
Slp hold time (from SCKp↑) Note 2	tSIH2			1/fMCK + 62		ns
Delay time from SCKp↓ to SOp output Note 3	tKS02	C = 30 pF Note 4	2.7 V ≤ EVDD0 ≤ 5.5 V		2/fMCK + 66	ns
			2.4 V ≤ EVDD0 ≤ 5.5 V		2/fMCK + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		400 Note 1	kHz
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Data setup time (reception)	$t_{\text{SU: DAT}}$	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 220$ Note 2		ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	$1/f_{\text{MCK}} + 580$ Note 2		ns
Data hold time (transmission)	$t_{\text{HD: DAT}}$	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	0	1420	ns

Note 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.**Note 2.** Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

- (3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI20		0		EV_{DD0}	V
		Internal reference voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} Note 3			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} Note 3			V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

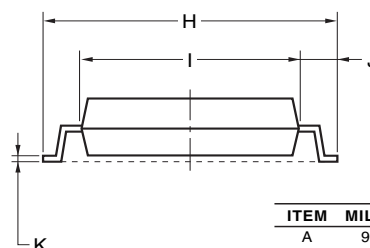
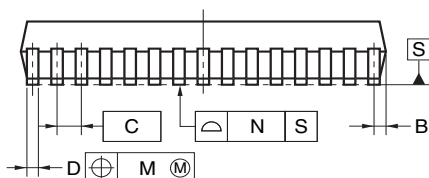
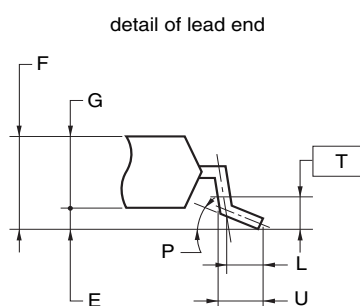
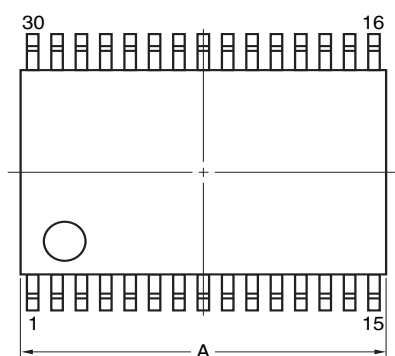
Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

4. PACKAGE DRAWINGS

4.1 30-pin products

R5F104AAASP, R5F104ACASP, R5F104ADASP, R5F104AEASP, R5F104AFASP, R5F104AGASP
 R5F104AADSP, R5F104ACDSP, R5F104ADDSP, R5F104AEDSP, R5F104AFDSP, R5F104AGDSP
 R5F104AAGSP, R5F104ACGSP, R5F104ADGSP, R5F104AEGSP, R5F104AFGSP, R5F104AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



NOTE

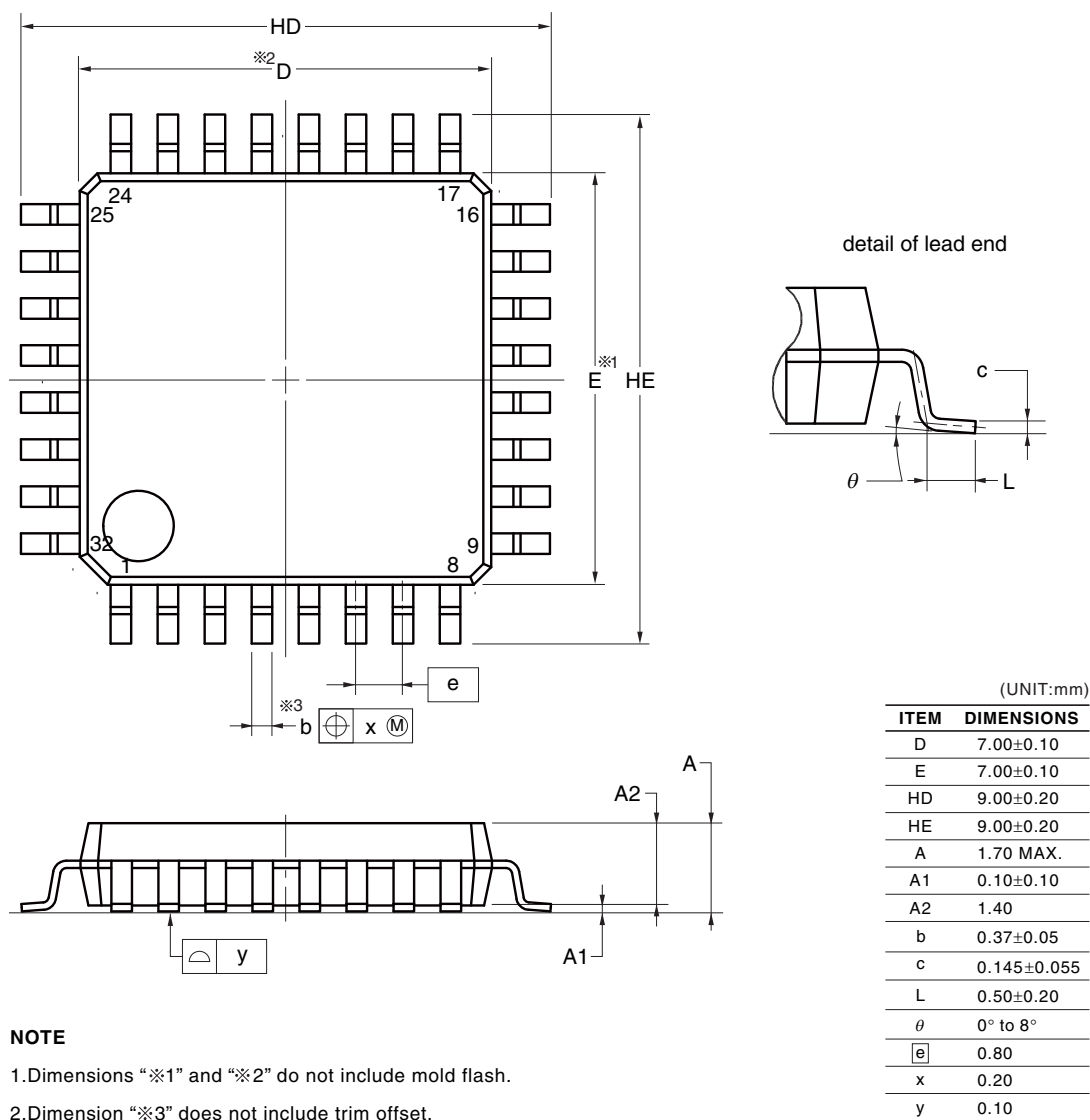
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

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R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP
 R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BDFP, R5F104BGDFP
 R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2



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